

UNISONIC TECHNOLOGIES CO., LTD

6NM70-Q

Preliminary

6.0A, 700V N-CHANNEL SUPER-JUNCTION MOSFET

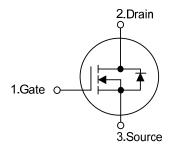
DESCRIPTION

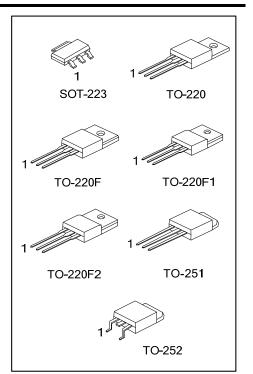
The **UTC 6NM70-Q** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

FEATURES

- * $R_{DS(ON)}$ < 1.44 Ω @ V_{GS} = 10V, I_D =3.0A
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL



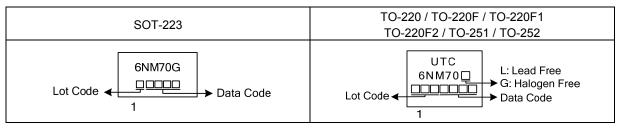


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	ORDERING	INFORMATION

Orderin	Deekege	Pin Assignment			Deaking		
Lead Free	Halogen Free	Package	1	2	3	Packing	
-	6NM70G-AA3-R	SOT-223	G	D	S	Tape Reel	
6NM70L-TA3-T	6NM70G-TA3-T	TO-220	G	D	S	Tube	
6NM70L-TF3-T	6NM70G-TF3-T	TO-220F	G	D	S	Tube	
6NM70L-TF1-T	6NM70G-TF1-T	TO-220F1	G	D	S	Tube	
6NM70L-TF2-T	6NM70G-TF2-T	TO-220F2	G	D	S	Tube	
6NM70L-TM3-T	6NM70G-TM3-T	TO-251	G	D	S	Tube	
6NM70L-TN3-R	6NM70G-TN3-R	TO-252	G	D	S	Tape Reel	
Note: Pin Assignment: G: Gate D: Drain S: Source							
6NM70 <u>G-AA3</u> -Ŗ	(1) T: Tube, R: Tape Reel						
	- (1)Packing Type	(2) AA3: SOT-223, TA3: TO-220, TF3: TO-220F,					
	- (2)Package Type	TF1: TO-220F1, TF2: TO-220F2, TM3: TO-251,					
	TN3: TO-252						
	(3) L: Lead Free, G: Halogen Free and Lead Free						

6NM70-Q

MARKING





■ ABSOLUTE MAXIMUM RATINGS (T_c = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V _{DSS}	700	V	
Gate-Source Voltage		V _{GSS}	±30	V	
Drain Current	Continuous	I _D	6.0	А	
Drain Current	Pulsed (Note 2)	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	А		
Avalanche Current (No	te 2)	I _{AR}	1.3	А	
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	123	mJ	
Peak Diode Recovery of	dv/dt (Note 4)	dv/dt	3.9	V/ns	
	SOT-223		5	W	
	TO-220		125	W	
Power Dissipation	TO-220F/TO-220F1 TO-220F2	P _D	40	W	
	TO-251/TO-252		55	W	
Junction Temperature		TJ	+150	°C	
Storage Temperature		T _{STG}	-55 ~ +150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied. 2. Repetitive Rating : Pulse width limited by maximum junction temperature.

- 3. L=145mH, I_{AS} =1.3A, V_{DD} =50V, R_G =25 Ω , Starting T_J = 25°C
- 4. $I_{SD} \leq 6.0A$, $di/dt \leq 200A/\mu s$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^{\circ}C$

THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT	
	SOT-223		150		
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2	θ_{JA}	62.5	°C/W	
	TO-251/TO-252		110		
	SOT-223		25		
	TO-220		1.0		
Junction to Case	TO-220F/TO-220F1 TO-220F2	θ _{JC}	3.13	°C/W	
	TO-251/TO-252		2.27		



■ ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

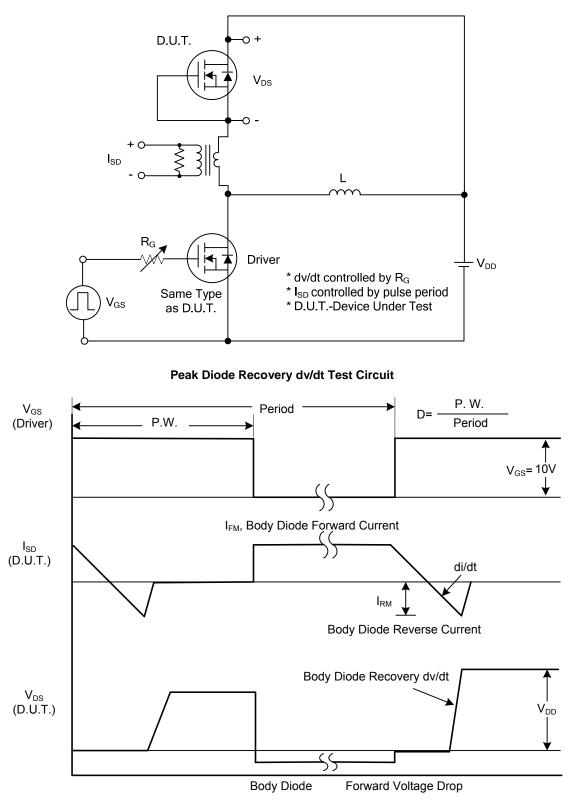
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS		01111202				110.00	0.111	
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0V, I _D = 250µA	700			V	
Drain-Source Leakage Current		I _{DSS}	$V_{DS} = 700V, V_{GS} = 0V$			10	μA	
	Forward	- I _{GSS}	$V_{GS} = 30V, V_{DS} = 0V$			100	nA	
Gate-Source Leakage Current	Reverse		$V_{GS} = -30V, V_{DS} = 0V$			-100	nA	
ON CHARACTERISTICS								
Gate Threshold Voltage		V _{GS(TH)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.5		4.5	V	
Static Drain-Source On-State Res	istance	R _{DS(ON)}	V _{GS} = 10V, I _D =3.0A			1.44	Ω	
DYNAMIC CHARACTERISTICS						_		
Input Capacitance		CISS			330		рF	
Output Capacitance		Coss	V _{GS} =0V, V _{DS} =25V, f =1MHz		215		рF	
Reverse Transfer Capacitance		C _{RSS}			20		рF	
SWITCHING CHARACTERISTICS								
Total Gate Charge (Note 1)		Q_{G}	V _{DS} =50V, V _{GS} =10V, I _D =1.3A		50		nC	
Gate to Source Charge		Q_{GS}	$I_{G}=100\mu A$ (Note 1, 2)		4.0		nC	
Gate to Drain Charge		Q_{GD}	IG-100μΑ (Note 1, 2)		11		nC	
Turn-ON Delay Time (Note 1)		t _{D (ON)}			36		ns	
Rise Time		t _R	V _{DD} =30V, V _{GS} =10V, I _D =0.5A,		65		ns	
Turn-OFF Delay Time		t _{D(OFF)}	R _G =25Ω (Note 1, 2)		140		ns	
Fall-Time		t _F			45		ns	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Maximum Body-Diode Continuous Current		ls				6.0	Α	
Maximum Body-Diode Pulsed Current		I _{SM}				24	А	
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I _S =6.0A, V _{GS} =0V			1.4	V	
Body Diode Reverse Recovery Time (Note 1)		t _{rr}	I _S =6.0A, V _{GS} =0V,		310		nS	
Body Diode Reverse Recovery Cl	narge	Qrr	dI _F /dt=200A/µs		2.7		μC	

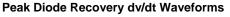
Notes: 1. Pulse Test: Pulse width \leq 300µs, Duty cycle \leq 2%.

2. Essentially independent of operating temperature.



TEST CIRCUITS AND WAVEFORMS





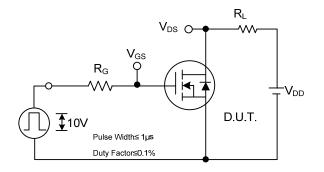


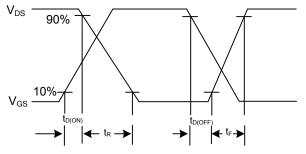
 V_{GS}

10V

Q_{GS}

TEST CIRCUITS AND WAVEFORMS (Cont.)



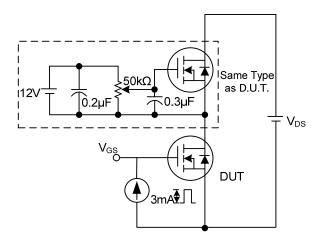


Switching Test Circuit

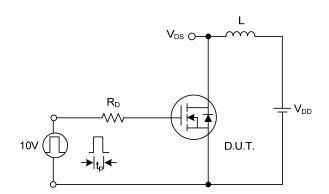


 Q_G

 Q_{GD}



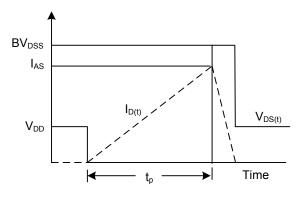
Gate Charge Test Circuit



Unclamped Inductive Switching Test Circuit

Gate Charge Waveform

Charge



Unclamped Inductive Switching Waveforms



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